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Contents

	Preface	<i>page</i> xi	
1	Introduction to Electromigration References		
2	Fundamentals of Electromigration	8	
	2.1 Introduction	8	
	2.2 Thermodynamic Description of Electromigration	8	
	2.3 Kinetic Analysis of Solute Effect on EM in Binary Alloys	10	
	2.4 Theory of Electromigration	15	
	2.5 Electromigration in Bulk Materials	19	
	2.6 Summary	29	
	References	29	
3	Thermal Stress Characteristics and Stress-Induced Void Formation		
	in Aluminum and Copper Interconnects	34	
	3.1 Technology Impact and Stress Effect on Electromigration	34	
	3.2 Effect of Passivation on Thermal Stress Characteristics in		
	Interconnect Lines	38	
	3.3 Thermal Stress Measurements by X-Ray Diffraction for Passivated		
	Metal Lines	41	
	3.4 Thermal Stress Characteristics and Effect of Dielectric Passivation on		
	Cu Damascene Lines	48	
	3.5 Stress Relaxation and Stress-Induced Void Formation in Passivated		
	Al Lines	55	
	3.6 Stress Relaxation and Passivation Effects in Cu Damascene Films and Lines	62	
	3.7 Stress-Induced Void Formation in Cu Damascene Line Structures	70	
	3.8 Summary	74	
	References	75	
4	Stress Evolution and Damage Formation in Confined Metal Lines under		
	Electric Stressing: 1D Analysis	80	
	4.1 Introduction	80	
	4.2 Kinetics of EM-Induced Mass Transport and Stress Evolution in		
	Confined Metal Lines	81	

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Cambridge University Press & Assessment 978-1-107-03238-5 — Electromigration in Metals Paul S. Ho , Chao-Kun Hu , Martin Gall , Valeriy Sukharev Table of Contents <u>More Information</u>

viii	Contents			
	4.2	Vienting of FM Induced Fundation of Vienness Distribution in		
	4.3	Kinetics of EM-Induced Evolution of Vacancy Distribution in Interconnect Segments	87	
	4.4	EM-Induced Stress Evolution in a Confined Metal Line:	87	
	4.4	Korhonen's Equation	88	
	4.5	Analytical Solutions for the 1D Korhonen Equation	93	
	4.6	Critical Stress for Void Formation	97	
	4.7	An Approximate Derivation of the Void Nucleation Time	99	
	4.8	Postvoiding Stress and Void Size Evolutions in Confined		
		Metal Lines	103	
	4.9	Voiding-Induced Degradation of Resistance of Metal Lines	109	
	4.10		111	
	4.11	-		
		1D Modeling	114	
	4.12	Summary	119	
		rences	120	
5	Electromigration in Cu Interconnect Structures			
	5.1	Introduction	127	
	5.2	Microstructure	129	
	5.3	Resistivity	131	
	5.4	Mass Transport and Damage Formation in Cu		
		Damascene Structures	135	
		The Blech Short-Length Effect	163	
	5.6	EM Lifetime Scaling Rule	164	
	5.7	Methods to Improve EM Reliability of the Cu Interconnect	166	
	5.8	EM through Various Technology Nodes	193	
	5.9	Summary	195	
	Refe	rences	196	
6	Scaling Effects on Microstructure of Cu and Co Nanointerconnects			
		Introduction	203	
	6.2	Precession Electron Diffraction Microscopy	204	
	6.3	Scaling Effect on the Microstructure of Cu Interconnects	208	
	6.4	Scaling Effect on the Microstructure of Co Interconnects	219	
	6.5	Monte Carlo Simulation of the Microstructure Evolution		
		in Nanointerconnects	225	
	6.6	Simulation Results for Copper Interconnects	234	
	6.7	Simulation Results for Cobalt Interconnects	239	
	6.8	Simulated Bamboo–Polygrain Structures and Implications for		
		EM Reliability	242	
	6.9	Summary	245	
	References		247	

Cambridge University Press & Assessment 978-1-107-03238-5 — Electromigration in Metals Paul S. Ho , Chao-Kun Hu , Martin Gall , Valeriy Sukharev Table of Contents <u>More Information</u>

		Contents	ix	
7	Analysis of Electromigration-Induced Stress Evolution and Voiding in Cu			
		ascene Lines with Microstructure	251	
	7.1	Introduction	251	
	7.2	EM-Induced Mass Transport	252	
	7.3	Evolution of Vacancy and Plated Atom Concentrations in a 3D		
		Confined Metal Line under Electric Current Stressing	254	
	7.4	Volumetric Stress Generated by Vacancies and Plated Atoms in a		
		Confined Metal Line	259	
	7.5	Evolution of Stress and Vacancy-Plated Atom Concentrations in a		
		Prevoiding State	263	
	7.6	Major Approaches to Modeling EM-Induced Stress Evolution		
		in Interconnects	266	
	7.7	Effect of Microstructure on EM-Induced Degradation in		
		Dual-Damascene Copper Interconnects	272	
	7.8	Experimental Studies of EM-Induced Voiding in Interconnects	294	
	7.9	Modeling of EM-Induced Void Motion and Shape Evolution	302	
	7.10	Numerical Techniques	306	
	7.11	EM-Induced Evolution of Stress-Induced Voids (SIV)	325	
	7.12		329	
	Refe	rences	330	
8	Massive-Scale Statistical Studies for Electromigration			
	8.1	Requirement for Massive Statistical EM Tests	338	
	8.2	Wheatstone Bridge Technique for Al Interconnects	339	
	8.3	Statistical Tests and Analysis for Cu Interconnects	354	
	8.4	Implications for EM Reliability	373	
	Refe	rences	375	
9	Asse	ssment of Electromigration Damage in Large On-Chip Power Grids	380	
	9.1	Introduction	380	
	9.2	Problems with the Standard Weakest Link Approximation for		
		On-Chip Power Grid EM Assessment	380	
	9.3	EM Assessment of Power Grids Based on Physical Modeling	390	
	9.4	EM Induced Stress Evolution under AC and Pulse Current Loads	391	
	9.5	On-Chip Power/Ground EM Assessment	397	
	9.6	Summary	409	
		rences	410	
	Inde:	x	414	

Colour plates section to be found between pp. 210 and 211